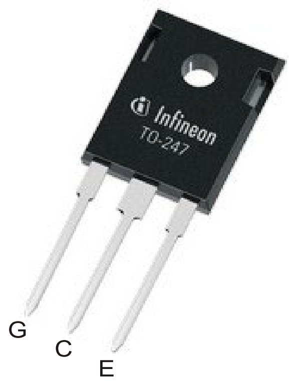
英飞凌短路坚固的 1200 V TRENCHSTOP™ IGBT 7 技术与软和快速恢复发射极控制 7 二极管

特性



- V_{CE} = 1200 V
- I_C = 8 A
- IGBT与全电流，软的及快恢复二极管合封
- 低饱和电压 V_{CEsat} = 2 V 在 T_{vj} = 175°C
- 针对硬开关拓扑进行了优化（2-L 逆变器、3-L NPC T 型……）
- 短路耐受性 8 µsec
- 广泛的 dv/dt 可控性
- 完整的产品品类和 PSpice 模型： http://www.infineon.com/igbt/

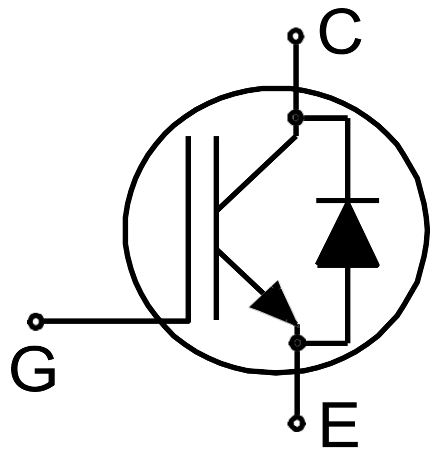
潜在应用

- 工业驱动
- 工业供电
- 太阳能逆变器

产品验证

- 符合JEDEC47/20/22相关测试的工业应用要求

描述



Type	Package	Marking
IKW08N120CS7	PG-TO247-3	K08MCS7

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 infineon.com 参考最新的英文版本（控制文档）。

目录

1 封装

表 1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5mm. (0.197in) from case	L_E			13.0		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6mm (0.063in.) from case for 10s			260	°C
Mounting torque , M3 screw Maximum of mounting process: 3	M				0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

2 IGBT

表2 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25$ °C		1200	V
DC collector current, limited by T_{vjmax}	I_C		$T_C = 25$ °C	21	A
			$T_C = 100$ °C	14	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}			24	A
Turn-off safe operating area		$V_{CE} \leq 1200$ V, $T_{vj} \leq 175$ °C		24	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 0.5$ µs, $D < 0.001$		±25	V
Short circuit withstand time	t_{SC}	$V_{CC} \leq 600$ V, $V_{GE} = 15$ V, Allowed number of short circuits < 1000, Time between short circuits ≥ 1.0 s, $T_{vj} = 150$ °C		8	µs
Power dissipation	P_{tot}		$T_C = 25$ °C	106	W
			$T_C = 100$ °C	53	

表3 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	$I_C = 8.0$ A, $V_{GE} = 15$ V	$T_{vj} = 25$ °C		1.65	2.00	V
			$T_{vj} = 175$ °C		2.00		

表 3 特征值（续）

Parameter	Symbol	Note or test condition		Values Min.	Values Typ.	Values Max.	Unit
Gate-emitter threshold voltage	V_{GEth}	I_C = 0.16 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.15	5.70	6.45	V
Zero gate voltage collector current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			40	µA
			T_{vj} = 175 °C		750		
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V				100	nA
Transconductance	g_{fs}	I_C = 8.0 A, V_{CE} = 20 V, T_{vj} = 175 °C			3.5		S
Short circuit collector current	I_{SC}	V_{CC} ≤ 600 V, V_{GE} = 15 V, t_{SC} ≤ 8 µs, Allowed number of short circuits < 1000 , Time between short circuits ≥ 1.0 s, T_{vj} = 25 °C			50		A
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			1.2		nF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			33		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			5.5		pF
Gate charge	Q_G	I_C = 8.0 A, V_{GE} = 15 V, V_{CE} = 960 V			52		nC
Turn-on delay time	t_{don}	V_{CE} = 600 V, V_{GE} = 15 V, R_{Gon} = 20.0 Ω, R_{Goff} = 20.0 Ω	T_{vj} = 25 °C, I_C = 8.0 A		17		ns
			T_{vj} = 175 °C, I_C = 8.0 A		16		
Rise time (inductive load)	t_r	V_{CE} = 600 V, V_{GE} = 15 V, R_{Gon} = 20.0 Ω, R_{Goff} = 20.0 Ω	T_{vj} = 25 °C, I_C = 8.0 A		12		ns
			T_{vj} = 175 °C, I_C = 8.0 A		15		
Turn-off delay time	t_{doff}	V_{CE} = 600 V, V_{GE} = 15 V, R_{Gon} = 20.0 Ω, R_{Goff} = 20.0 Ω	T_{vj} = 25 °C, I_C = 8.0 A		160		ns
			T_{vj} = 175 °C, I_C = 8.0 A		245		
Fall time (inductive load)	t_f	V_{CE} = 600 V, V_{GE} = 15 V, R_{Gon} = 20.0 Ω, R_{Goff} = 20.0 Ω	T_{vj} = 25 °C, I_C = 8.0 A		95		ns
			T_{vj} = 175 °C, I_C = 8.0 A		255		
Turn-on energy	E_{on}	V_{CE} = 600 V, V_{GE} = 15 V, R_{Gon} = 20.0 Ω, R_{Goff} = 20.0 Ω	T_{vj} = 25 °C, I_C = 8.0 A		0.37		mJ
			T_{vj} = 175 °C, I_C = 8.0 A		0.59		
Turn-off energy	E_{off}	V_{CE} = 600 V, V_{GE} = 15 V, R_{Gon} = 20.0 Ω, R_{Goff} = 20.0 Ω	T_{vj} = 25 °C, I_C = 8.0 A		0.40		mJ
			T_{vj} = 175 °C, I_C = 8.0 A		0.86		

表 3 特征值（续）

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Total switching energy	E_{ts}	V_{CE} = 600 V, V_{GE} = 15 V, R_{Gon} = 20.0 Ω, R_{Goff} = 20.0 Ω	T_{vj} = 25 °C, I_C = 8.0 A		0.77		mJ
			T_{vj} = 175 °C, I_C = 8.0 A		1.45		
IGBT thermal resistance, junction-case	R_{thjc}				1.05	1.42	K/W
Operating junction temperature	T_{vj}			-40		175	°C

3 二极管

表4 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj} ≥ 25 °C		1200	V
Diode forward current, limited by T_{vjmax}	I_F		T_C = 25 °C	18	A
			T_C = 100 °C	12	
Diode pulsed current, limited by T_{vjmax}	I_{Fpuls}			24	A
Power dissipation	P_{tot}		T_C = 25 °C	62	W
			T_C = 100 °C	31	

表5 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 8.0 A	T_{vj} = 25 °C		1.65	2.15	V
			T_{vj} = 175 °C		1.60		
Reverse leakage current	I_R	V_R = 1200 V	T_{vj} = 25 °C			40	µA
			T_{vj} = 175 °C		750		
Diode reverse recovery time	t_{rr}	V_R = 600 V, R_{Gon} = 20.0 Ω	T_{vj} = 25 °C, I_F = 8.0 A		130		ns
			T_{vj} = 175 °C, I_F = 8.0 A		210		
Diode reverse recovery charge	Q_{rr}	V_R = 600 V, R_{Gon} = 20.0 Ω	T_{vj} = 25 °C, I_F = 8.0 A		0.45		µC
			T_{vj} = 175 °C, I_F = 8.0 A		1.10		

表 5　　特征值（续）

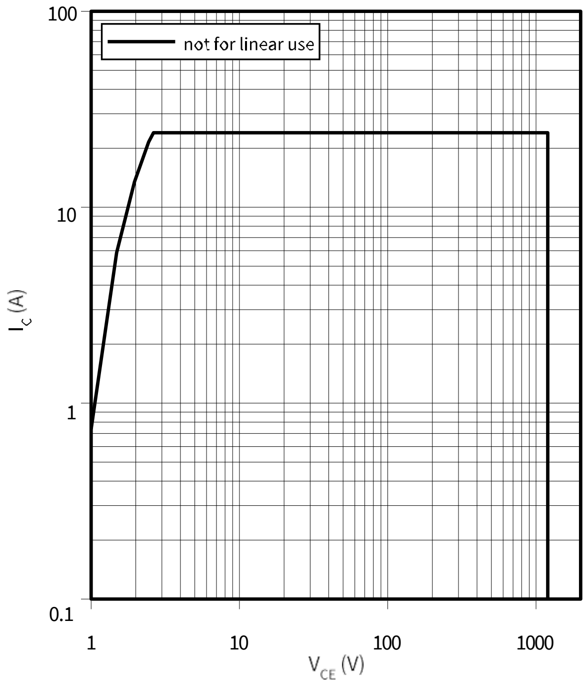
Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode peak reverse recovery current	I_{rrm}	V_R = 600 V, R_{Gon} = 20.0 Ω	T_{vj} = 25 °C, I_F = 8.0 A		9.0		A
			T_{vj} = 175 °C, I_F = 8.0 A		13.0		
Diode peak rate off fall of reverse recovery current	dI_{rr}/dt	V_R = 600 V, R_{Gon} = 20.0 Ω	T_{vj} = 25 °C, I_F = 8.0 A		-110		A/µs
			T_{vj} = 175 °C, I_F = 8.0 A		-95		
Reverse recovery energy	E_{rec}	V_R = 600 V, R_{Gon} = 20.0 Ω	T_{vj} = 25 °C, I_F = 8.0 A		0.13		mJ
			T_{vj} = 175 °C, I_F = 8.0 A		0.37		
Diode thermal resistance, junction-case	R_{thjc}				1.80	2.40	K/W
Operating junction temperature	T_{vj}			-40		175	°C

注意：为了获得最佳的使用寿命和可靠性，英飞凌建议运行条件不超过本数据手册中所述最大额定值的80%。

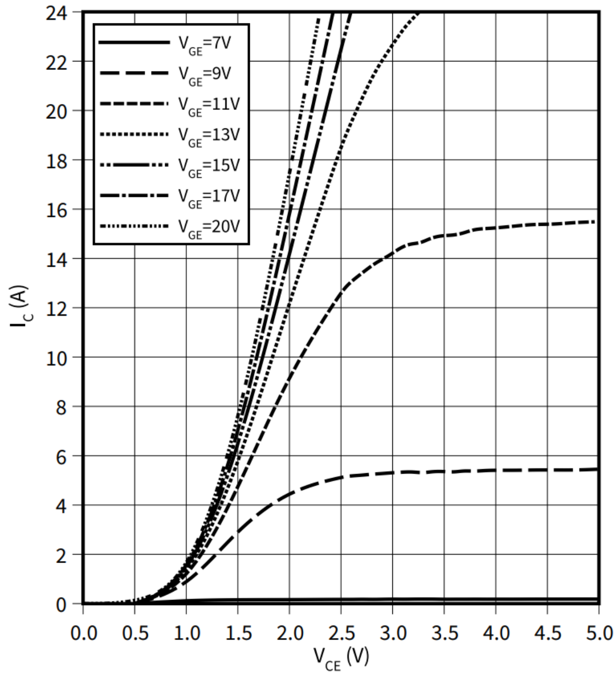
动态测试电路，寄生电感 L_σ = 30 nH, C_σ = 4 pF

4 特性图

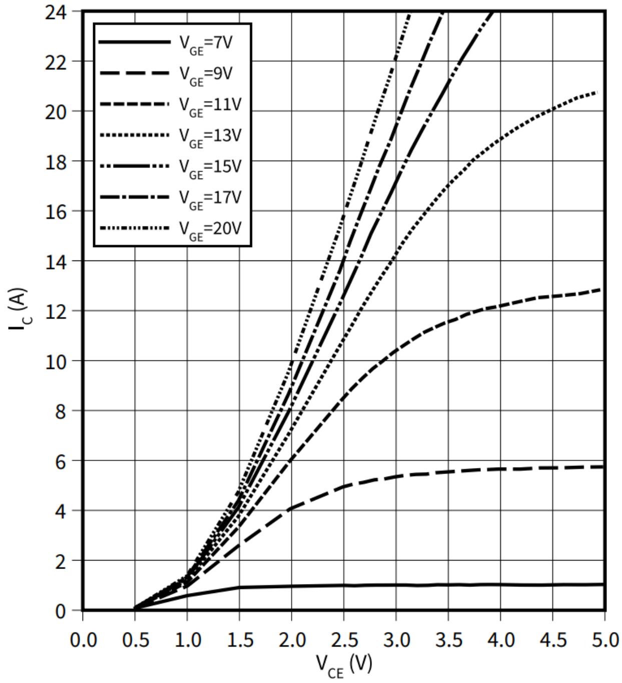
Reverse bias safe operating area, IGBT
$I_C = f(V_{CE})$
$T_{vj} \leq 175\ °C$, $V_{GE} = 15\ V$



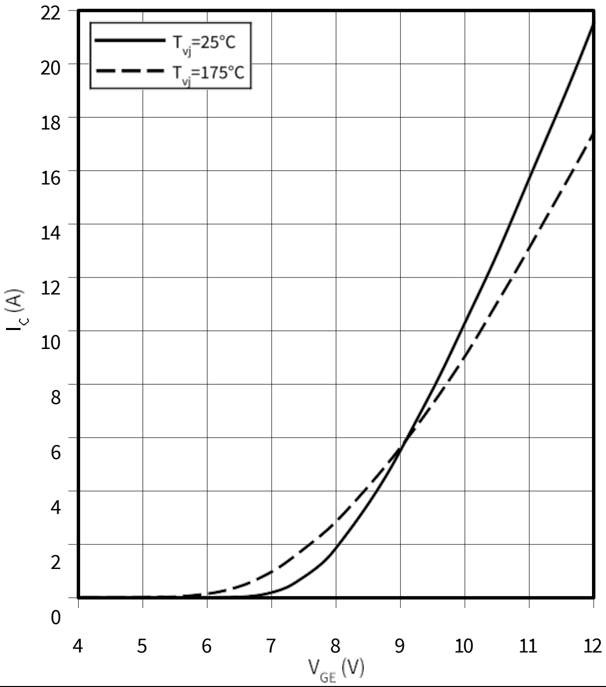
Typical output characteristic, IGBT
$I_C = f(V_{CE})$
$T_{vj} = 25\ °C$

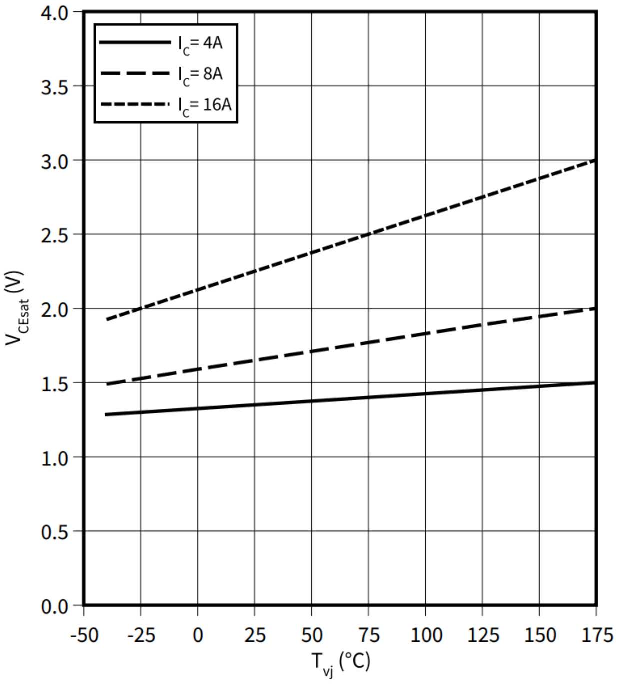
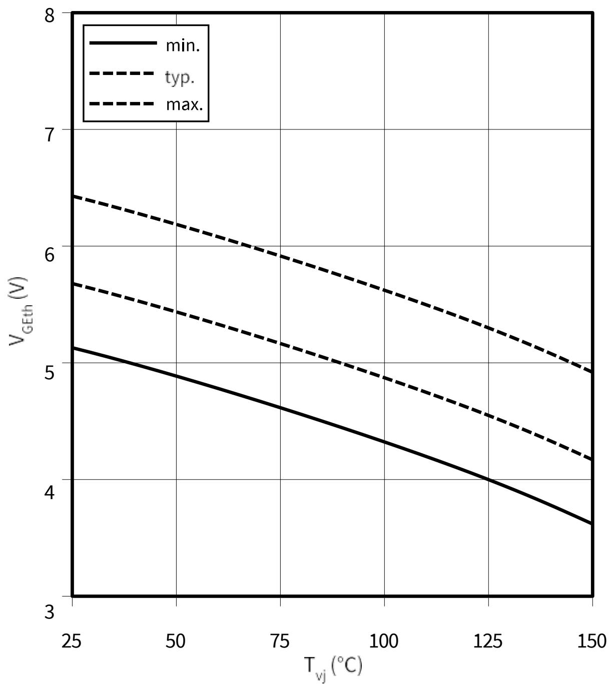
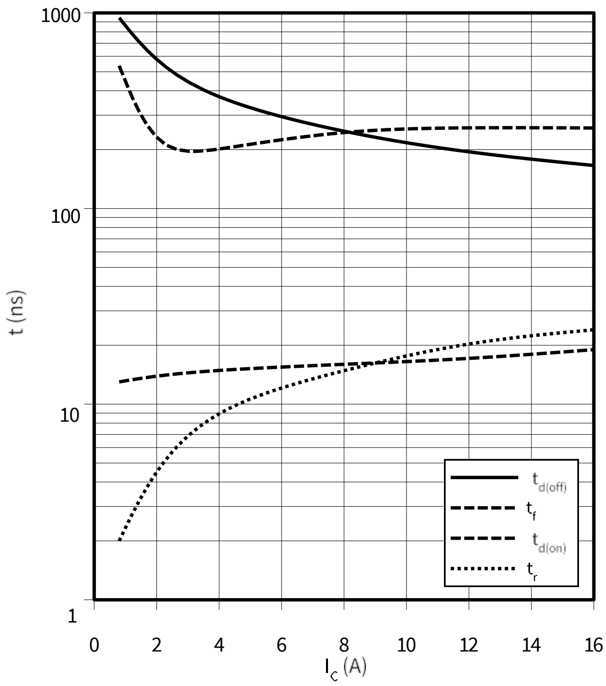
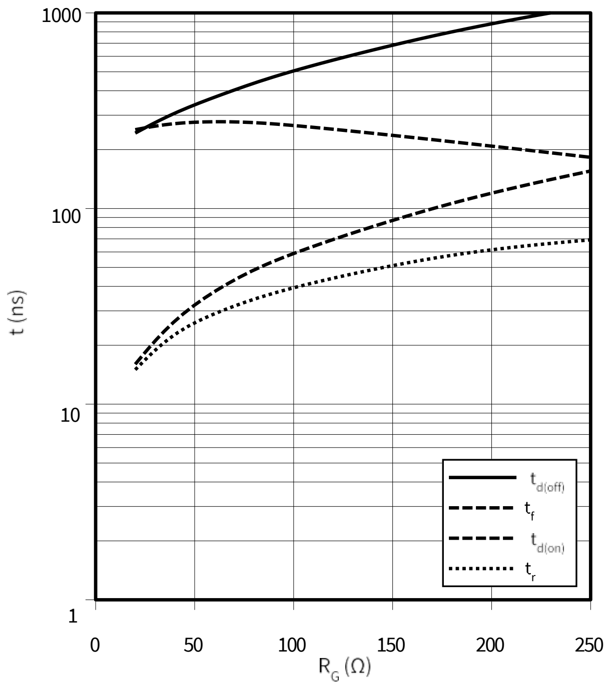


Typical output characteristic, IGBT
$I_C = f(V_{CE})$
$T_{vj} = 175\ °C$



Typical transfer characteristic, IGBT
$I_C = f(V_{GE})$
$V_{CE} = 20\ V$

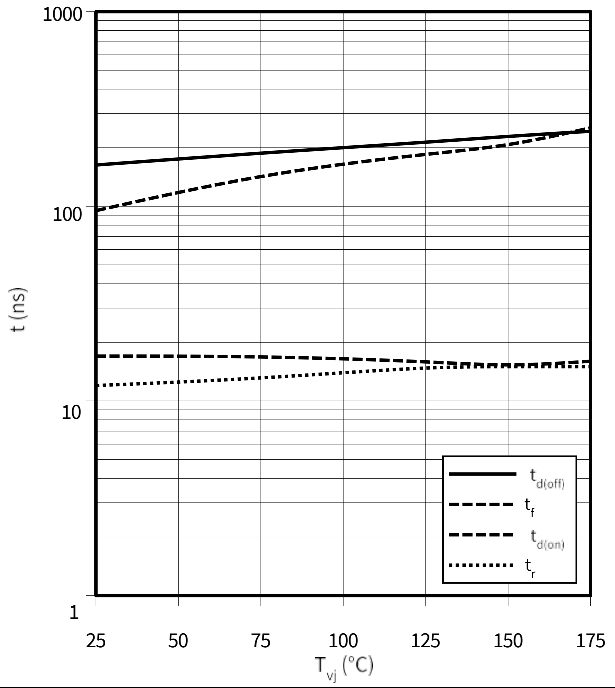


Typical collector-emitter saturation voltage as a function of junction temperature, IGBT $V_{CEsat} = f(T_{vj})$ $V_{GE} = 15$ V	**Gate-emitter threshold voltage as a function of junction temperature, IGBT** $V_{GEth} = f(T_{vj})$ $I_C = 0.16$ mA
	
Typical switching times as a function of collector current, IGBT $t = f(I_C)$ $V_{CE} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 20.0\ \Omega$	**Typical switching times as a function of gate resistor, IGBT** $t = f(R_G)$ $I_C = 8.0$ A, $V_{CE} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V
	

Typical switching times as a function of junction temperature, IGBT

$t = f(T_{vj})$

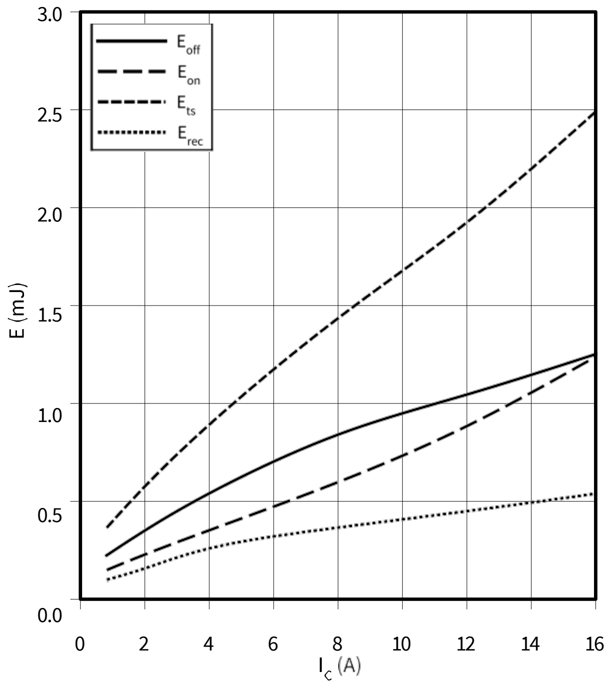
$I_C = 8.0$ A, $V_{CE} = 600$ V, $V_{GE} = 0/15$ V, $R_G = 20.0\ \Omega$



Typical switching energy losses as a function of collector current, IGBT

$E = f(I_C)$

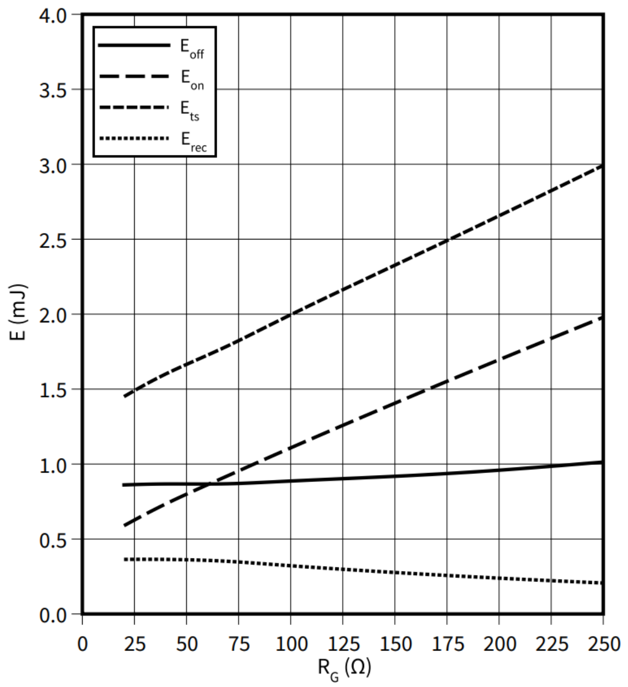
$V_{CE} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 20.0\ \Omega$



Typical switching energy losses as a function of gate resistor, IGBT

$E = f(R_G)$

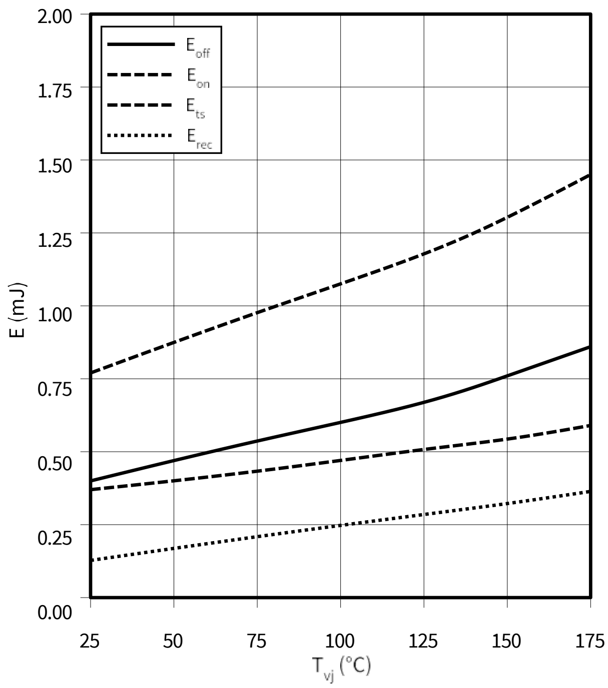
$I_C = 8.0$ A, $V_{CE} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V



Typical switching energy losses as a function of junction temperature, IGBT

$E = f(T_{vj})$

$I_C = 8.0$ A, $V_{CE} = 600$ V, $V_{GE} = 0/15$ V, $R_G = 20.0\ \Omega$

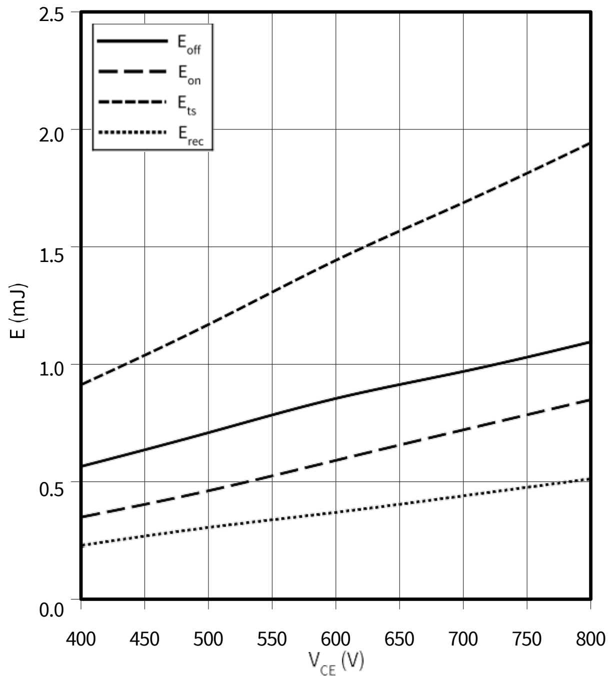


4 特征图

Typical switching energy losses as a function of collector emitter voltage, IGBT

$E = f(V_{CE})$

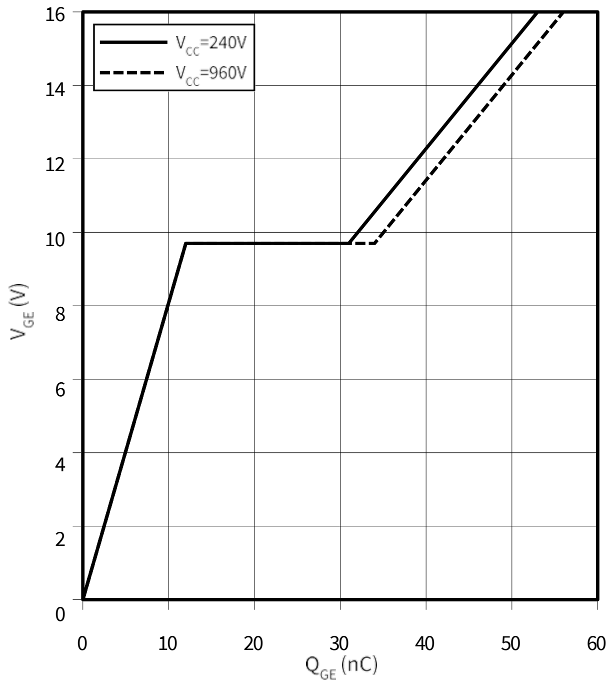
$I_C = 8.0$ A, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 20.0$ Ω



Typical gate charge, IGBT

$V_{GE} = f(Q_{GE})$

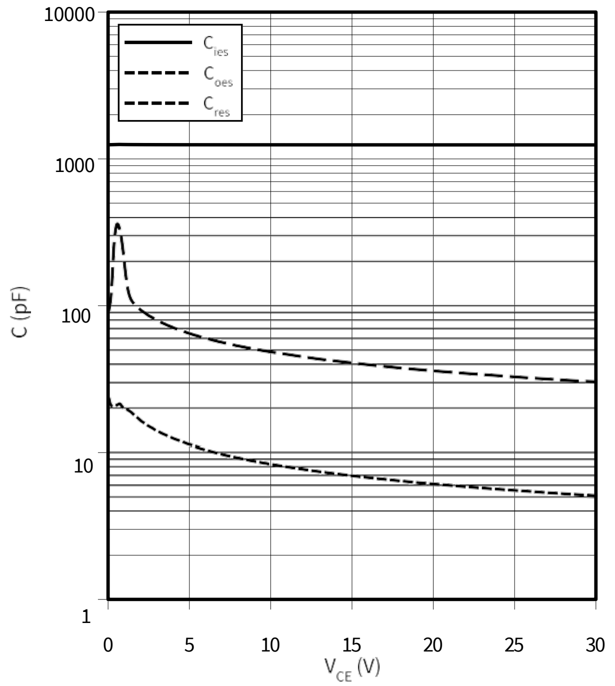
$I_C = 8.0$ A



Typical capacitance as a function of collector-emitter voltage, IGBT

$C = f(V_{CE})$

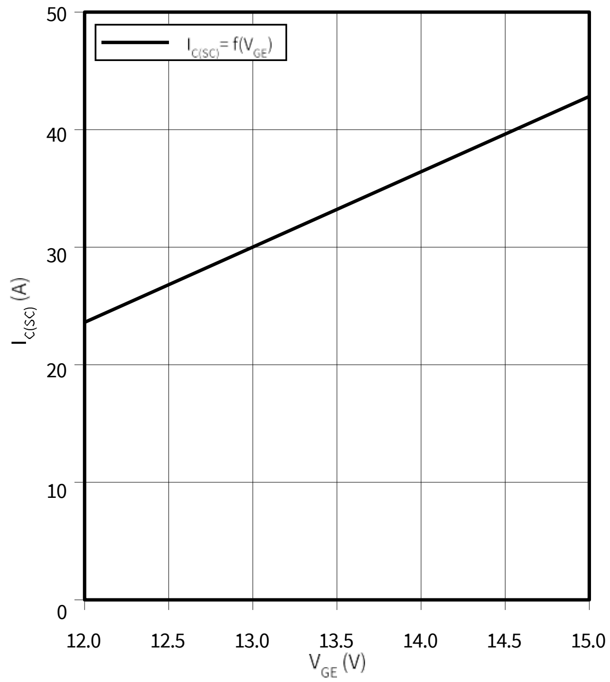
$f = 100$ kHz, $V_{GE} = 0$ V



Typical short circuit collector current as a function of gate-emitter voltage, IGBT

$I_{C(SC)} = f(V_{GE})$

$T_{vj} = 150$ °C, $V_{CC} = 600$ V

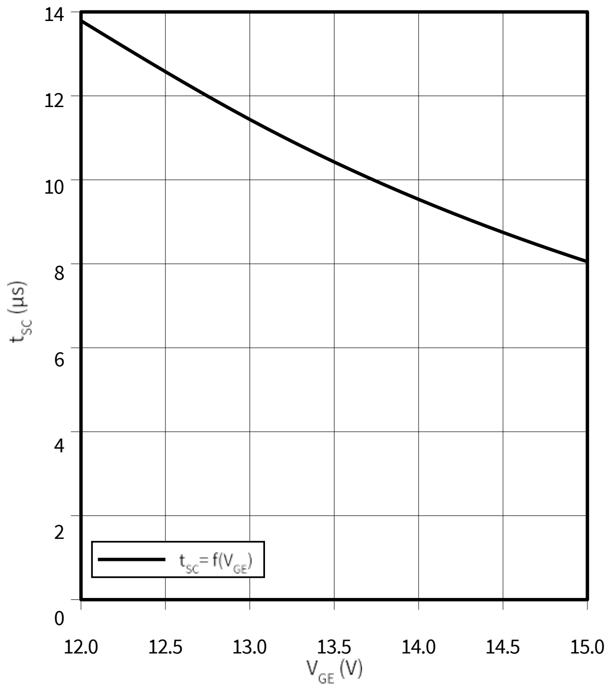


4 特征图

Short circuit withstand time as a function of gate-emitter voltage, IGBT

$t_{SC} = f(V_{GE})$

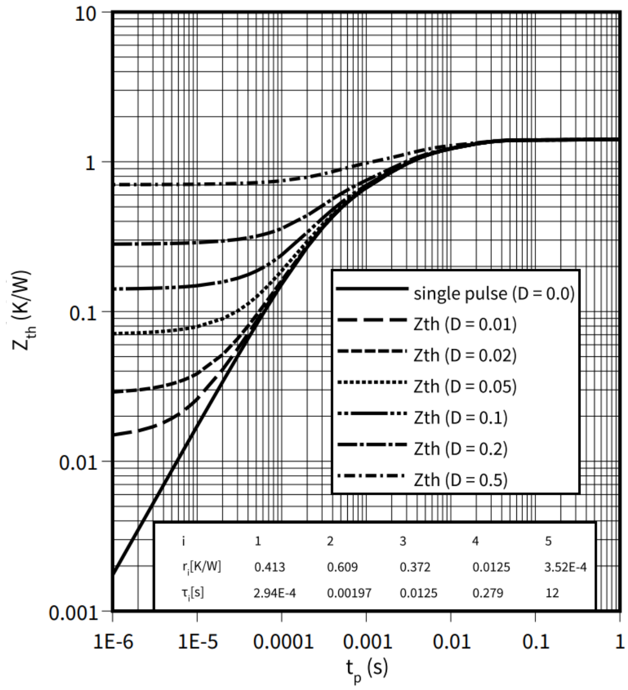
$T_{vj} \leq 150\ °C$, $V_{CC} = 600\ V$



IGBT transient thermal impedance, IGBT

$Z_{th} = f(t_p)$

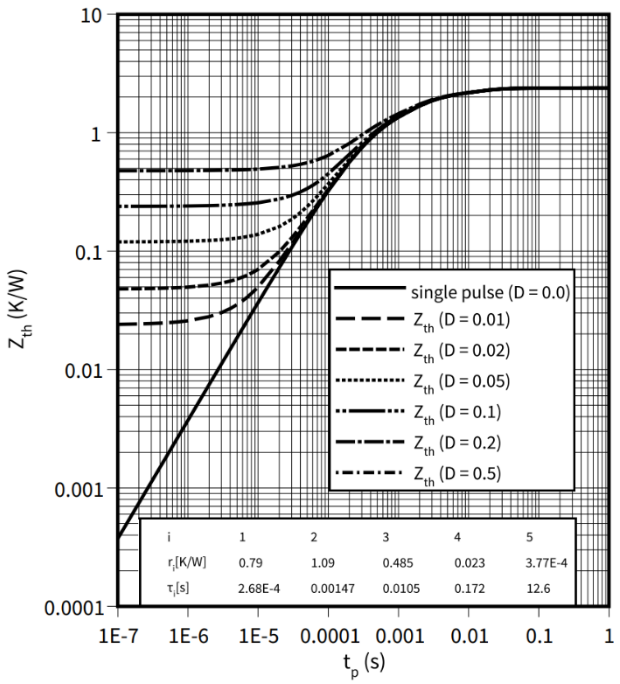
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width, Diode

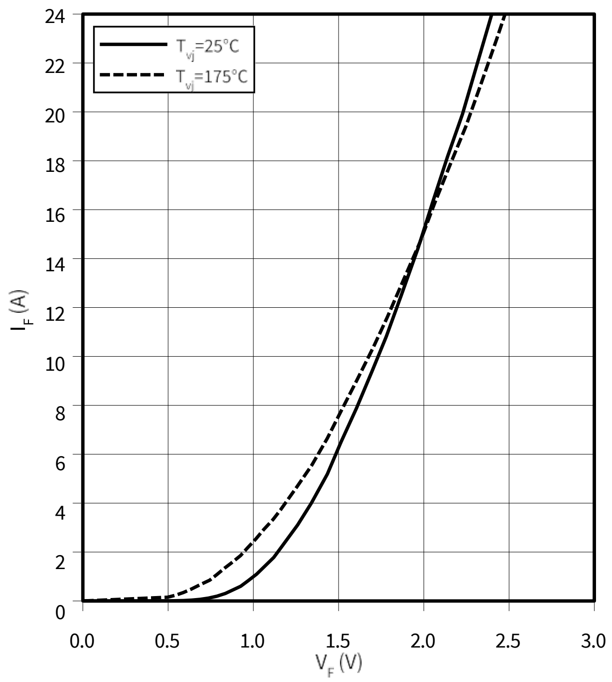
$Z_{th} = f(t_p)$

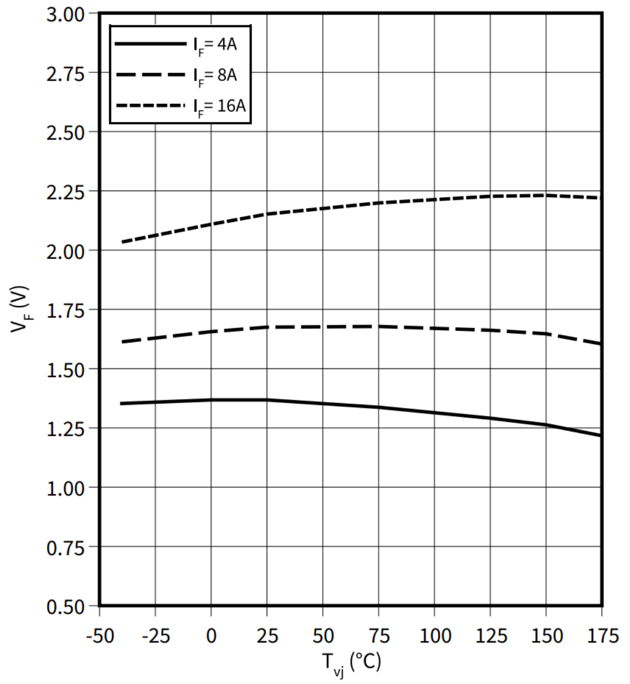
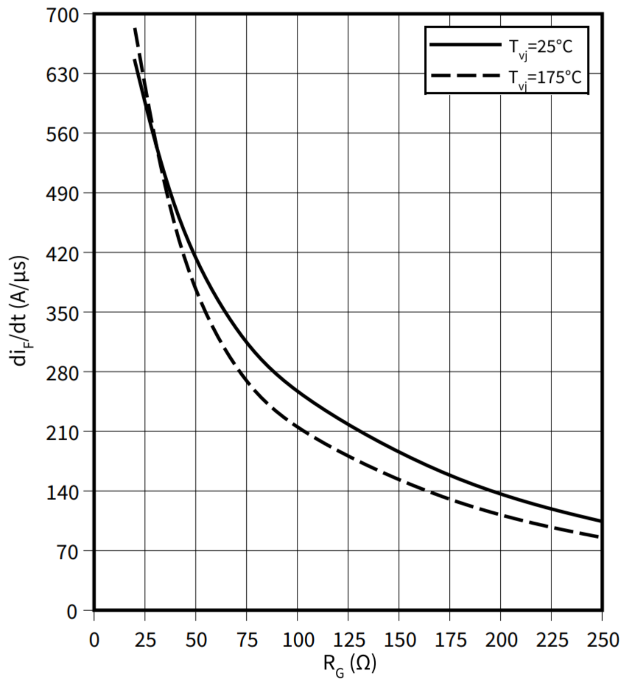
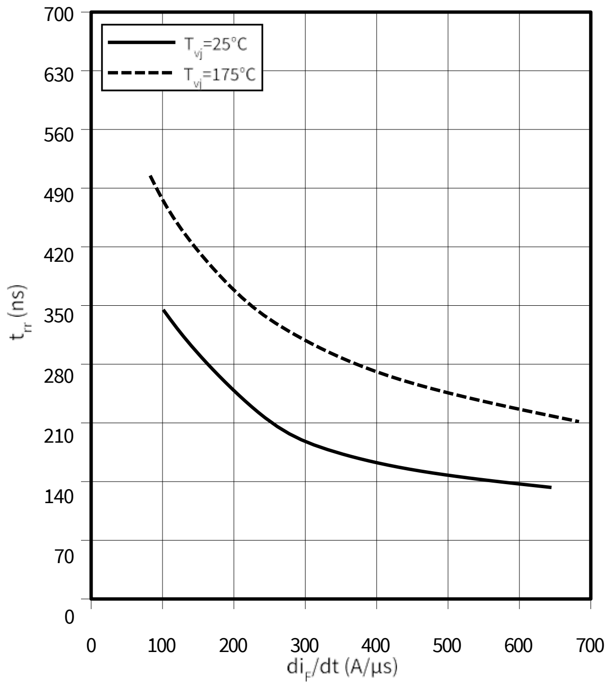
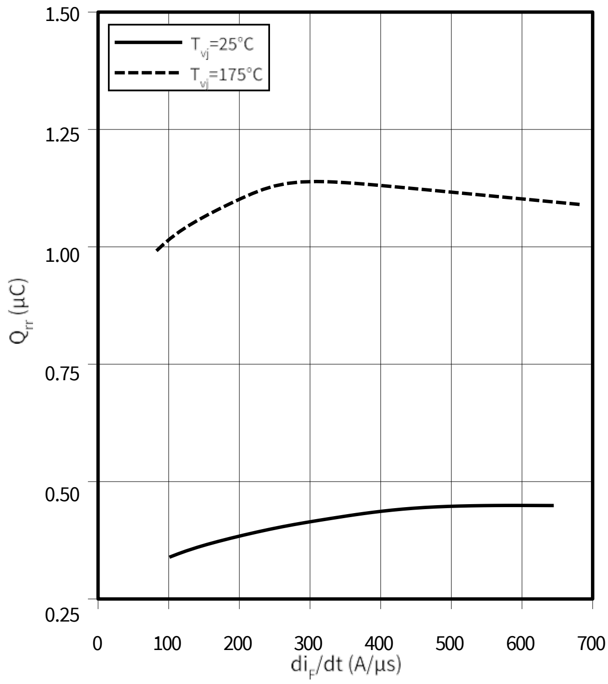
$D = t_p/T$



Typical diode forward current as a function of forward voltage, Diode

$I_F = f(V_F)$

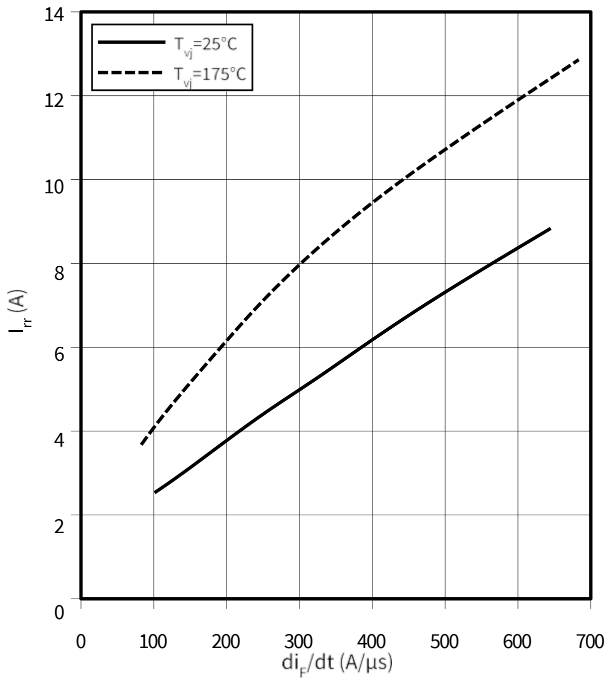


Typical diode forward voltage as a function of junction temperature, Diode $V_F = f(T_{vj})$	Typical diode current slope as a function of gate resistor, Diode $di_F/dt = f(R_G)$ $I_C = 8.0$ A, $V_{CE} = 600$ V, $V_{GE} = 0/15$ V
	
Typical reverse recovery time as a function of diode current slope, Diode $t_{rr} = f(di_F/dt)$ $V_R = 600$ V, $I_F = 8.0$ A	**Typical reverse recovery charge as a function of diode current slope, Diode** $Q_{rr} = f(di_F/dt)$ $V_R = 600$ V, $I_F = 8.0$ A
	

Typical reverse recovery current as a function of diode current slope, Diode

$I_{rr} = f(di_F/dt)$

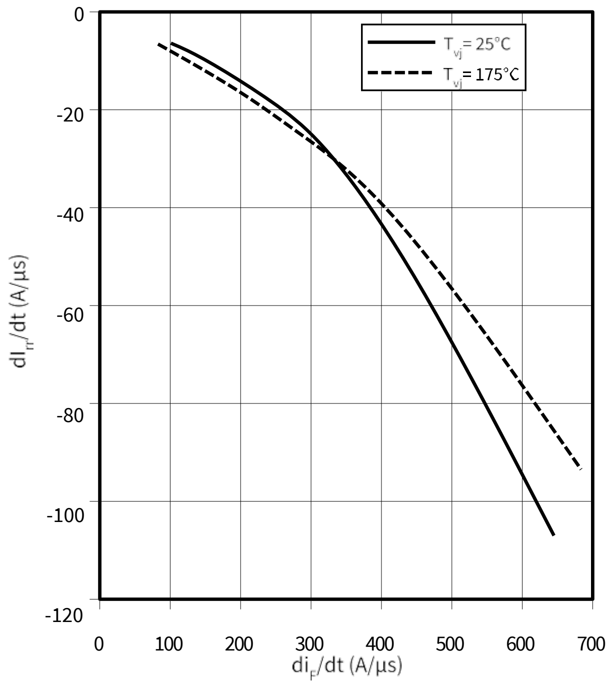
$V_R = 600\ V$, $I_F = 8.0\ A$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope, Diode

$dI_{rr}/dt = f(di_F/dt)$

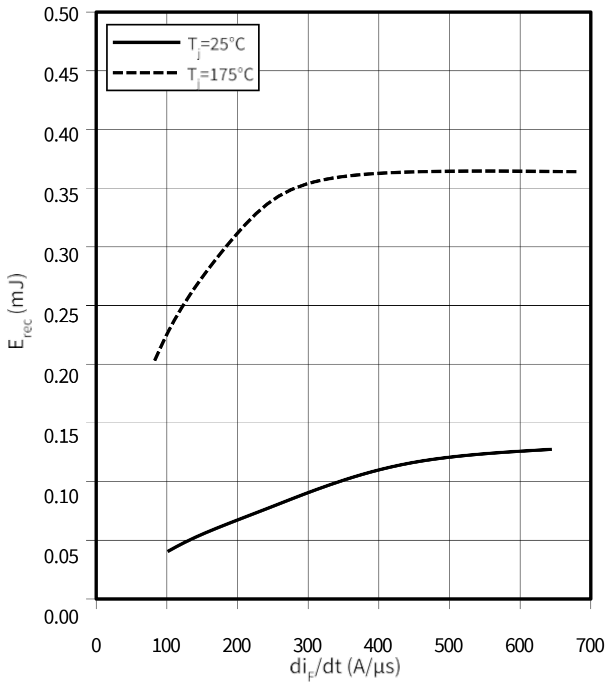
$V_R = 600\ V$, $I_F = 8.0\ A$



Typical reverse energy losses as a function of diode current slope, Diode

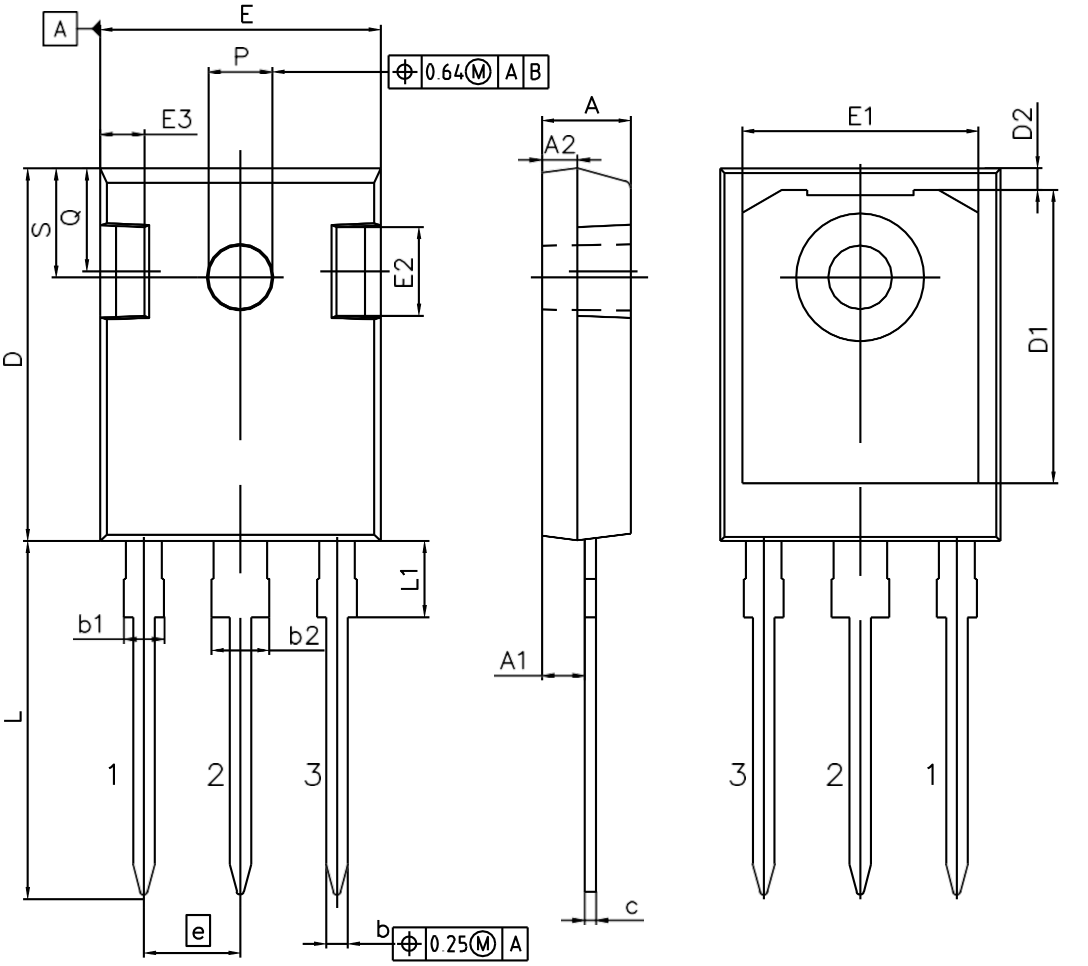
$E_{rec} = f(di_F/dt)$

$V_R = 600\ V$, $I_F = 8.0\ A$



5 封装外形

封装图 PG-TO247-3



DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.70	5.30
A1	2.20	2.60
A2	1.50	2.50
b	1.00	1.40
b1	1.60	2.41
b2	2.57	3.43
c	0.38	0.89
D	20.70	21.50
D1	13.08	17.65
D2	0.51	1.35
E	15.50	16.30
E1	12.38	14.15
E2	3.40	5.10
E3	1.00	2.60
e	5.44	
L	19.80	20.40
L1	3.85	4.50
P	3.50	3.70
Q	5.35	6.25
S	6.04	6.30

DOCUMENT NO. Z8B00003327
REVISION 06
SCALE 3:1 0 1 2 3 4 5mm
EUROPEAN PROJECTION
ISSUE DATE 25.07.2018

图 6.

6 测试条件

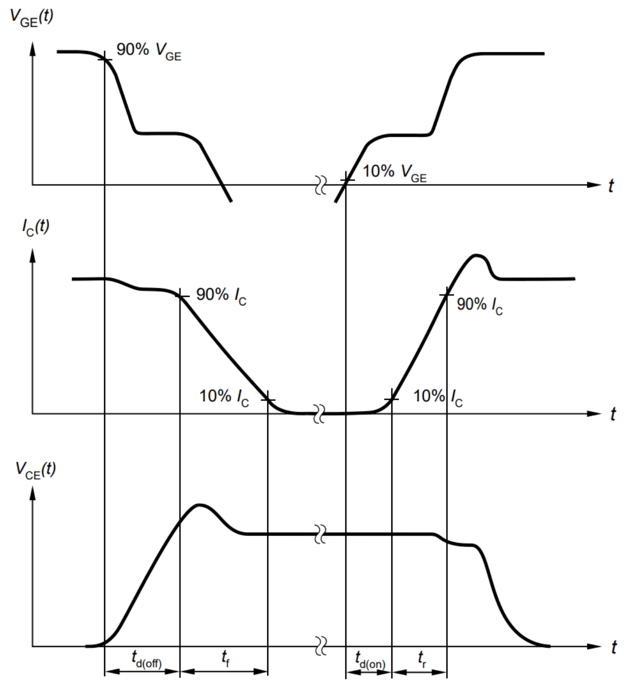


Figure A. **Definition of switching times**

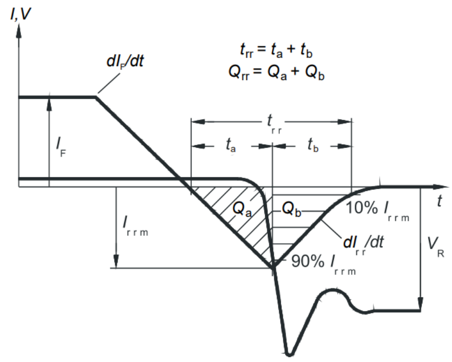


Figure C. **Definition of diode switching characteristics**

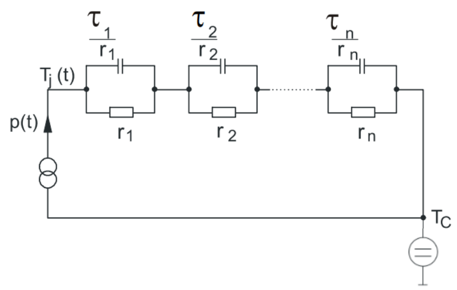


Figure D. **Thermal equivalent circuit**

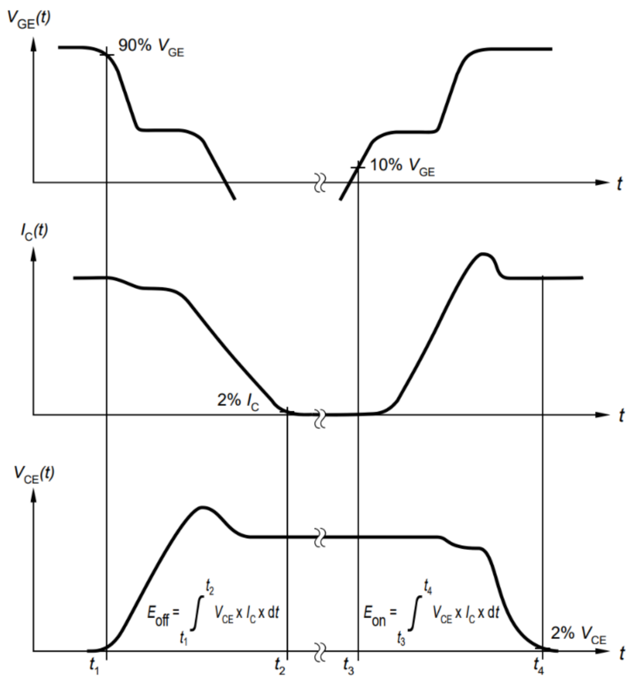


Figure B. **Definition of switching losses**

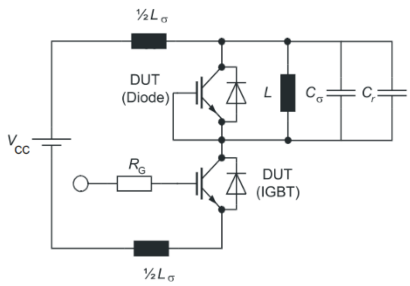


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

图 7

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